

Kindly amend claims 1-3 as follows:

b'  
EP  
c

1. (Twice Amended) A photodiode comprising: an optical detection portion for detecting an optical signal and outputting a photoelectric conversion signal, the optical detection portion having a semiconductor substrate of a first conductive type, a plurality of semiconductor layers of a second conductive type formed in spaced-apart relation in a surface of the semiconductor substrate, and a depletion layer formed in the semiconductor substrate by application of a reverse bias to the photodiode so as to surround the semiconductor layers, the depletion layer having an etched surface portion disposed between the semiconductor layers.

2. (Twice Amended) A photodiode according to claim 1; wherein a distance between the semiconductor layers is 0.5 to 2 times a width of the depletion layer.

3. (Amended) A photodiode according to claim 1; wherein the etched surface portion of the depletion layer comprises a wet-etched surface portion.

IN THE ABSTRACT:

Delete the abstract now of record and insert therefor the new abstract submitted herewith of on a separate sheet.